## Silicon N-Channel MOS FET

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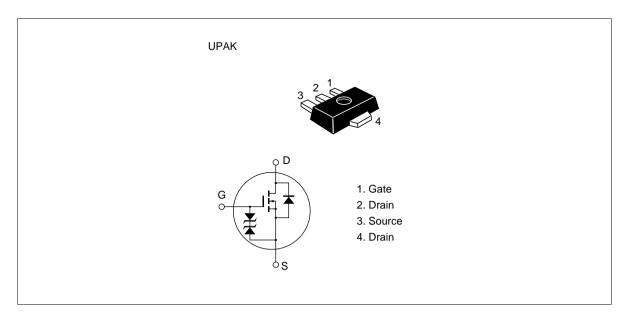
#### Application

High speed power switching

#### Features

- Low on-resistance
- High speed switching
- Low drive current
- 4 V gate drive device - can be driven from 5 V source.
- Suitable for DC DC converter, motor drive, power switch, solenoid drive

#### Outline





#### **Absolute Maximum Ratings** ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	60	V
Gate to source voltage	V <sub>GSS</sub>	±20	V
Drain current	I <sub>D</sub>	0.5	А
Drain peak current	L(pulse) *1	1.5	А
Body to drain diode reverse drain current	I <sub>DR</sub>	0.5	А
Channel dissipation	Pch*2	1	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. When using the alumina ceramic board ( $12.5 \times 20 \times 0.7$  mm)

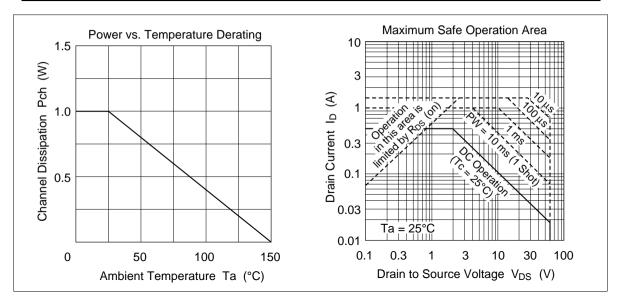
3. Marking is "EY".

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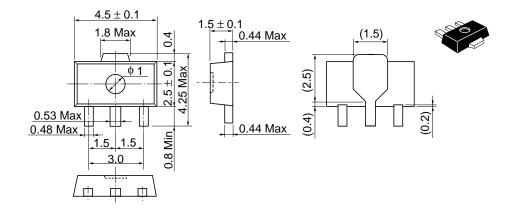
#### **Electrical Characteristics** (Ta = 25°C)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	60	_	_	V	$I_{\rm D} = 10$ mA, $V_{\rm GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	_	V	$I_{g} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	—	—	±10	μΑ	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	50	μΑ	$V_{\rm DS} = 50 \ V, \ V_{\rm GS} = 0$
Gate to source cutoff voltage	$V_{\text{GS(off)}}$	1.0	—	2.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{\text{DS(on)}}$	_	1.3	1.7	Ω	$I_{\rm D} = 0.3$ A, $V_{\rm GS} = 10$ V $^{*1}$
		_	1.8	2.5	Ω	$I_{\rm D} = 0.3$ A, $V_{\rm GS} = 4$ V * <sup>1</sup>
Forward transfer admittance	y <sub>fs</sub>	0.25	0.38	_	S	$I_{\rm D} = 0.3$ A, $V_{\rm DS} = 10$ V $^{*1}$
Input capacitance	Ciss	_	30	_	pF	$V_{\rm DS} = 10 \ V, \ V_{\rm GS} = 0,$
Output capacitance	Coss	_	13	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	4		pF	
Turn-on delay time	t <sub>d(on)</sub>	_	3		ns	$I_{\rm D} = 0.3 \text{ A}, V_{\rm GS} = 10 \text{ V},$
Rise time	t,	_	8	_	ns	R <sub>L</sub> = 100 Ω
Turn-off delay time	t <sub>d(off)</sub>	_	18	_	ns	_
Fall time	t <sub>f</sub>	_	14	_	ns	
Body to drain diode forward voltage	$V_{DF}$	—	1	—	V	$I_F = 0.5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>		45	—	ns	$I_F = 0.5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu \text{s}$
Note 1. Pulse test						

See characteristic curve of 2SK1336.



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Hitachi Code	UPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.050 g

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